

μ PA2561T1H

R07DS0006EJ0100

MOS FIELD EFFECT TRANSISTOR

Rev.1.00
Jul 08, 2010

Description

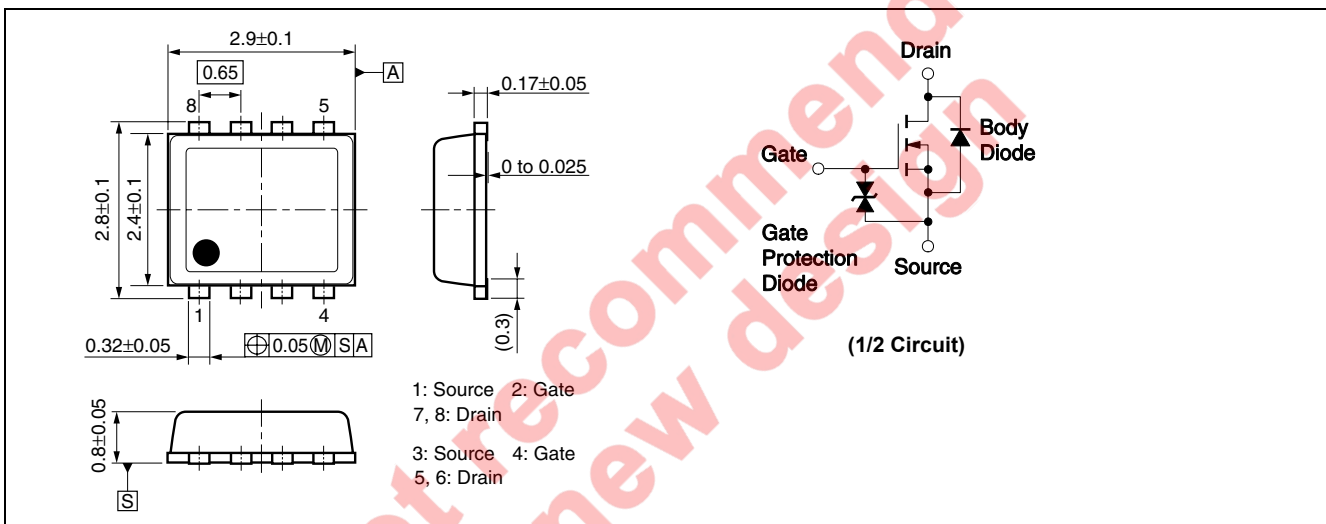
The μ PA2561 is Dual N-channel MOSFETs designed for back light inverters and power management applications of portable equipments. Dual N-channel MOSFETs are assembled in one package, to contribute minimize the equipments.

Features

- 2.5 V drive available
- Low on-state resistance
 - $R_{DS(on)1} = 50 \text{ m}\Omega \text{ MAX.}$ ($V_{GS} = 4.5 \text{ V}, I_D = 2 \text{ A}$)
 - $R_{DS(on)2} = 65 \text{ m}\Omega \text{ MAX.}$ ($V_{GS} = 2.5 \text{ V}, I_D = 2 \text{ A}$)

Package Drawing (Unit: mm)

Equivalent Circuit



Ordering Information

Part No.	Lead Plating	Packing	Package
μ PA2561T1H-T1-AT ^{Note}	Pure Sn	8 mm Embossed Taping	8-pin VSOE (2429)
μ PA2561T1H-T2-AT ^{Note}		3000 p/reel	

Note: This product does not contain Pb in external electrode and other parts.

Marking: 2561

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Drain to Source Voltage ($V_{GS} = 0 \text{ V}$)	V_{DSS}	20	V
Gate to Source Voltage ($V_{DS} = 0 \text{ V}$)	V_{GSS}	± 12	V
Drain Current (DC)	$I_{D(DC)}$	± 4.5	A
Drain Current (pulse) ^{Note1}	$I_{D(pulse)}$	± 18	A
Total Power Dissipation (1 unit, 5s) ^{Note2}	P_{T1}	1.5	W
Total Power Dissipation (2 unit, 5s) ^{Note2}	P_{T2}	2.2	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to + 150	$^\circ\text{C}$

Notes 1. $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 1\%$

2. Mounted on FR-4 board of 25.4 mm x 25.4 mm x 0.8 mm

Remark The diode connected between the gate and source of the transistor serves as a protector against ESD.
 When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

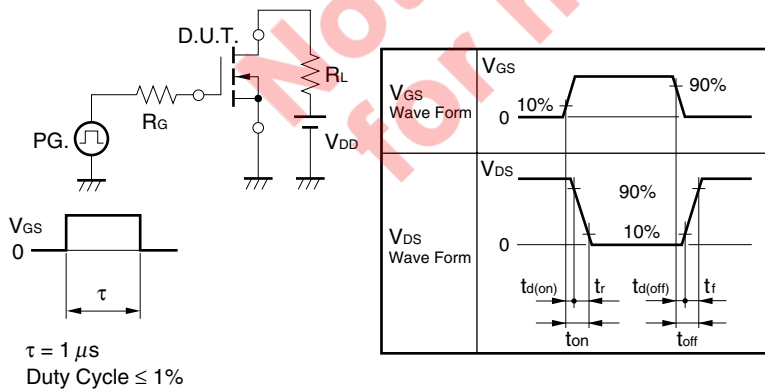
Caution This product is electrostatic-sensitive device due to low ESD capability and should be handled with caution for electrostatic discharge.

Electrical Characteristics (T_A = 25°C)

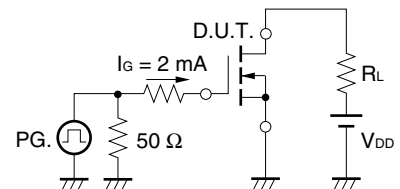
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Zero Gate Voltage Drain Current	I _{DSS}			1	μA	V _{DS} = 20 V, V _{GS} = 0 V
Gate Leakage Current	I _{GSS}			±10	μA	V _{GS} = ±12 V, V _{DS} = 0 V
Gate to Source Cut-off Voltage	V _{GS(off)}	0.5		1.5	V	V _{DS} = 10 V, I _D = 1 mA
Forward Transfer Admittance ^{Note}	y _{fs}	2.0			S	V _{DS} = 10 V, I _D = 2 A
Drain to Source On-state Resistance ^{Note}	R _{DS(on)1}		29	50	mΩ	V _{GS} = 4.5 V, I _D = 2 A
	R _{DS(on)2}		41	65	mΩ	V _{GS} = 2.5 V, I _D = 2 A
Input Capacitance	C _{iss}		455		pF	V _{DS} = 10 V
Output Capacitance	C _{oss}		75		pF	V _{GS} = 0 V
Reverse Transfer Capacitance	C _{rss}		47		pF	f = 1.0 MHz
Turn-on Delay Time	t _{d(on)}		8.0		ns	V _{DD} = 10 V, I _D = 2 A,
Rise Time	t _r		8.0		ns	V _{GS} = 4.5 V,
Turn-off Delay Time	t _{d(off)}		20		ns	R _G = 6 Ω
Fall Time	t _f		6.0		ns	
Total Gate Charge	Q _G		5.4		nC	V _{DD} = 16 V,
Gate to Source Charge	Q _{GS}		0.9		nC	V _{GS} = 4.5 V,
Gate to Drain Charge	Q _{GD}		1.6		nC	I _D = 4 A
Diode Forward Voltage ^{Note}	V _{F(S-D)}		0.85		V	I _F = 4 A, V _{GS} = 0 V

Note: Pulsed

TEST CIRCUIT 1 SWITCHING TIME

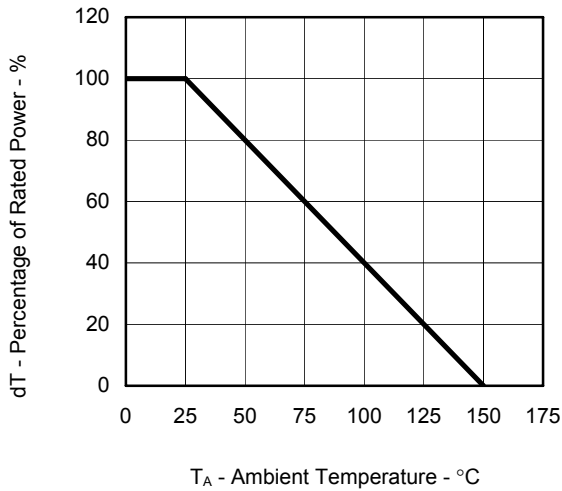


TEST CIRCUIT 2 GATE CHARGE

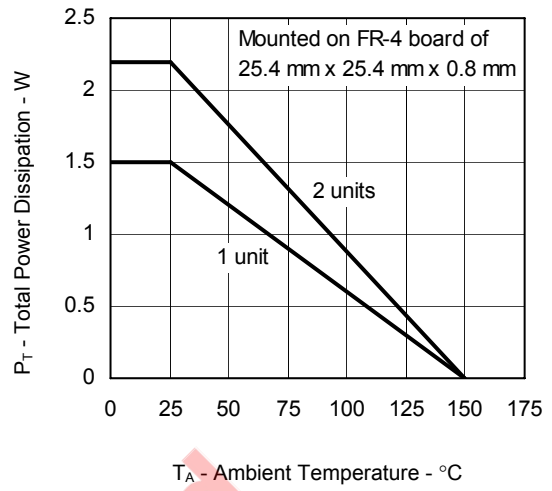


Typical Characteristics (T_A = 25°C)

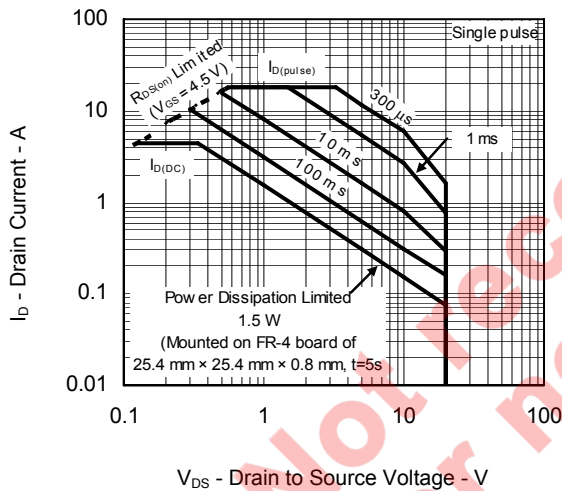
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



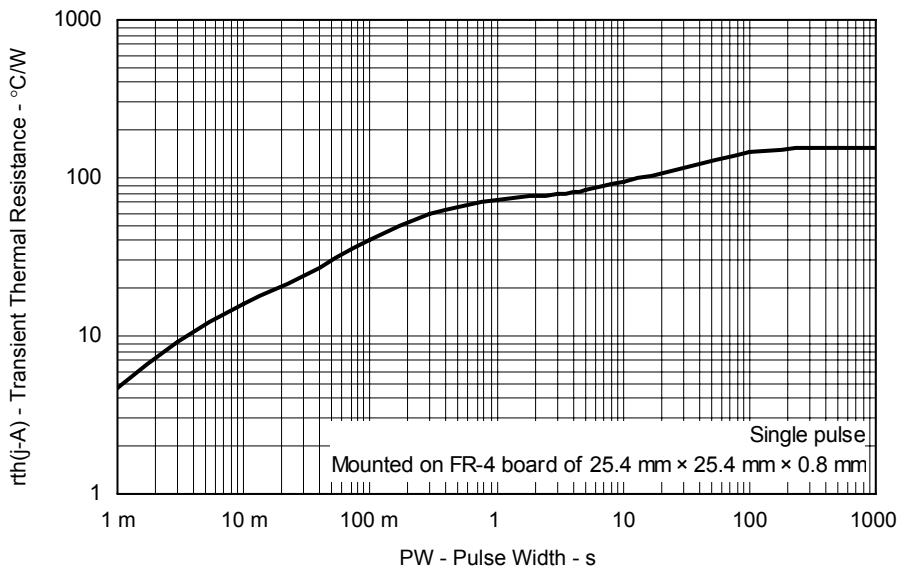
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



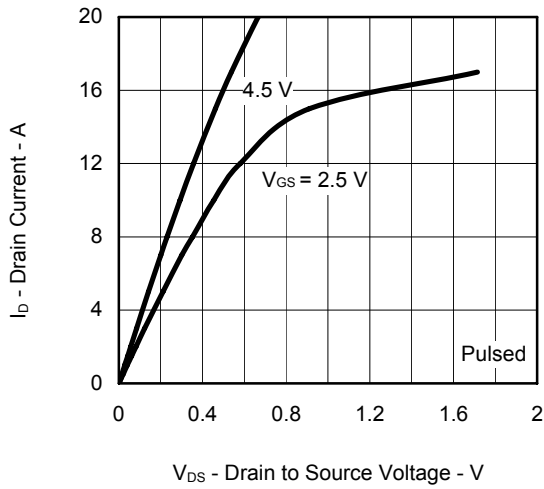
FORWARD BIAS SAFE OPERATING AREA



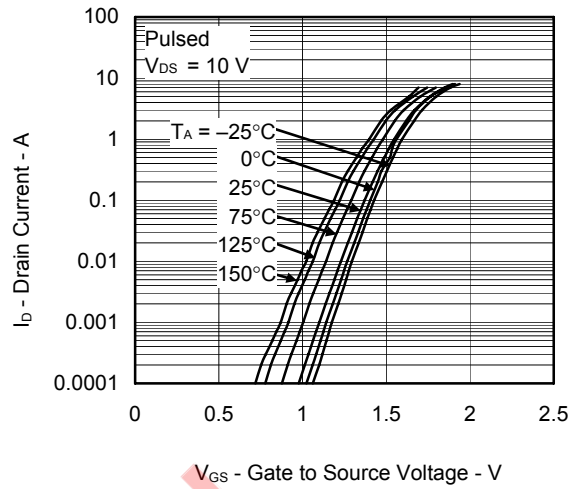
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



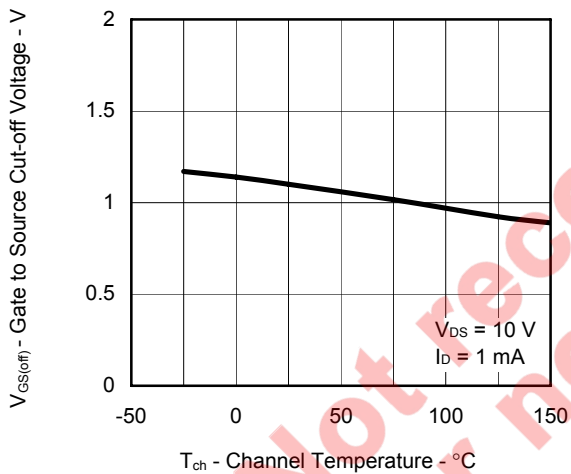
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



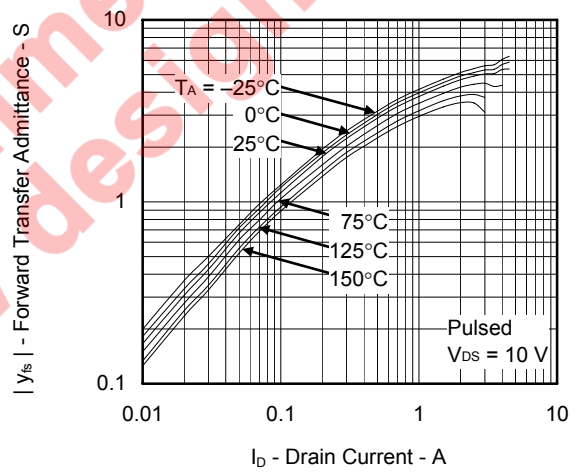
FORWARD TRANSFER CHARACTERISTICS



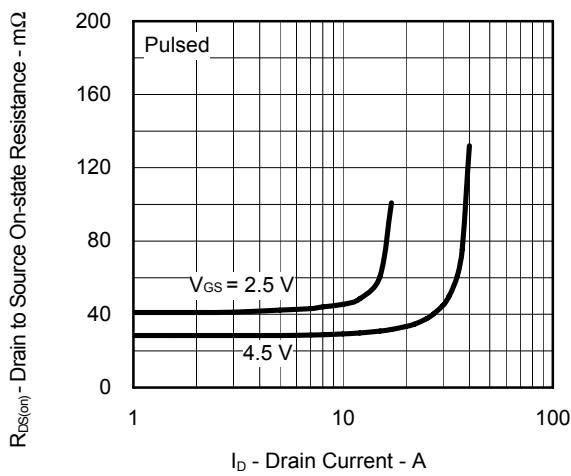
GATE TO SOURCE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



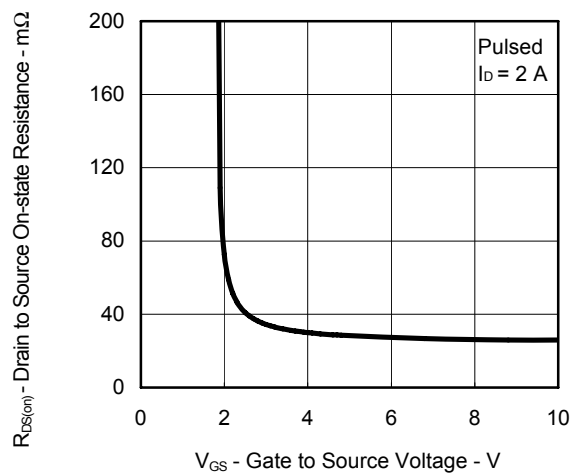
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



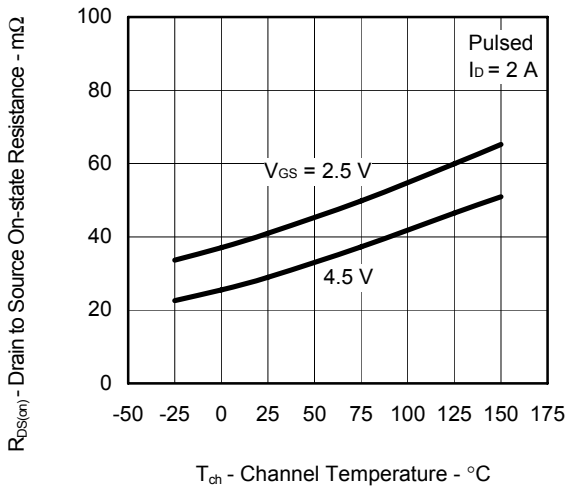
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



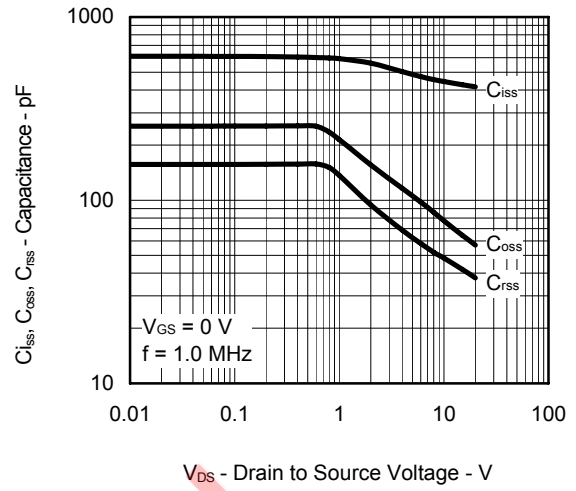
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



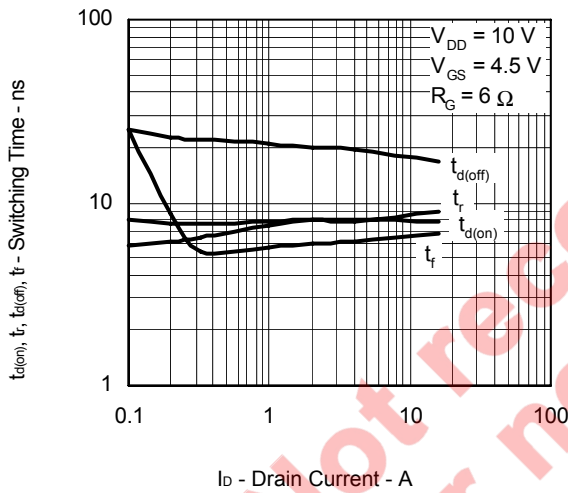
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



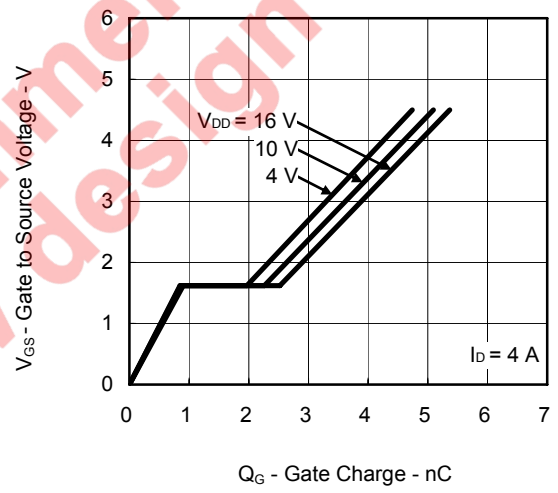
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



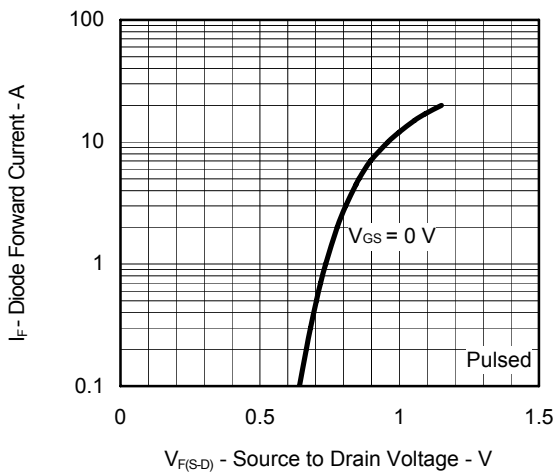
SWITCHING CHARACTERISTICS



DYNAMIC INPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE



Revision History	μ PA2561T1H
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Rev.	Date	Description	
		Page	Summary
1.00	Jul 08, 2010	-	First Edition issued

**Not recommend
for new design**

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Renesas Electronics America Inc.
2880 Scott Boulevard Santa Clara, CA 95050-2554, U.S.A.
Tel: +1-408-588-6000, Fax: +1-408-588-6130

Renesas Electronics Canada Limited
1101 Nicholson Road, Newmarket, Ontario L3Y 9C3, Canada
Tel: +1-905-898-5441, Fax: +1-905-898-3220

Renesas Electronics Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K
Tel: +44-1628-585-100, Fax: +44-1628-585-900

Renesas Electronics Europe GmbH
Arcadiastrasse 10, 40472 Düsseldorf, Germany
Tel: +49-211-6503-0, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd.
7th Floor, Quantum Plaza, No.27 ZhiChunLu Haidian District, Beijing 100083, P.R.China
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

Renesas Electronics (Shanghai) Co., Ltd.
Unit 204, 205, AZIA Center, No.1233 Lujiazui Ring Rd., Pudong District, Shanghai 200120, China
Tel: +86-21-5877-1818, Fax: +86-21-6887-7858 / -7898

Renesas Electronics Hong Kong Limited
Unit 1601-1613, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2886-9318, Fax: +852-2886-9022/9044

Renesas Electronics Taiwan Co., Ltd.
7F, No. 363 Fu Shing North Road Taipei, Taiwan, R.O.C.
Tel: +886-2-8175-9600, Fax: +886-2-8175-9670

Renesas Electronics Singapore Pte. Ltd.
1 HarbourFront Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: +65-6213-0200, Fax: +65-6278-8001

Renesas Electronics Malaysia Sdn.Bhd.
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: +60-3-7955-9390, Fax: +60-3-7955-9510

Renesas Electronics Korea Co., Ltd.
11F., Samik Laviel'or Bldg., 720-2 Yeoksam-Dong, Kangnam-Ku, Seoul 135-080, Korea
Tel: +82-2-558-3737, Fax: +82-2-558-5141